

UNIVERSITY OF OSLO

Faculty of mathematics and natural sciences

Examination in INF9425 — Projects in analog/mixed-signal
CMOS construction

Day of examination: 7. June 2012

Examination hours: 14:30–18:30

This problem set consists of 6 pages.

Appendices: None

Permitted aids: Any written material and approved calculator

Please make sure that your copy of the problem set is complete before you attempt to answer anything.

Contents

1	Oscillators and PLLs	20 %	page 1
2	Switched capacitor circuits	25 %	page 2
3	Flash ADCs	25 %	page 4
4	Pipelined ADCs	20 %	page 5
5	Current Steering DACs	10 %	page 5

Problem 1 Oscillators and PLLs 20 %

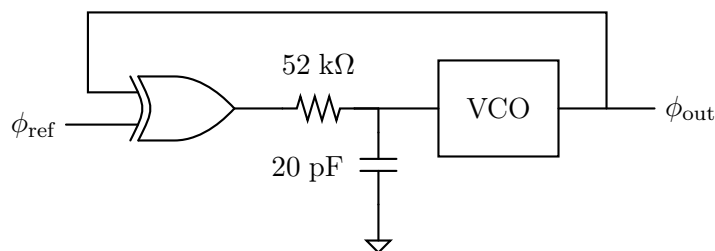


Figure 1: Type I PLL

1a Phase error 5 %

The PLL in figure 1 is a so called “type I PLL” with an XOR phase detector. The supply voltage is 1 V, the VCO has a center frequency of $f_0 = 1.9$ GHz and $K_{VCO} = 120 \frac{\text{kHz}}{\text{V}}$. If the reference frequency is $f_{\text{ref}} = f_0 + 40$ kHz, what is the phase difference between the reference signal and the output signal assuming the PLL is in lock?

(Continued on page 2.)

1b Dynamic properties 5 %

What is the damping ratio, ζ , and the natural frequency, ω_n , in this case?

1c Lock range 5 %

Will the PLL be able to achieve lock in all cases? Why or why not?

1d Delay line 5 %

The VCO is reconfigured as a delay line for use in a DLL. Using the parameters from the previous problems, what is the nominal delay?

Problem 2 Switched capacitor circuits 25 %

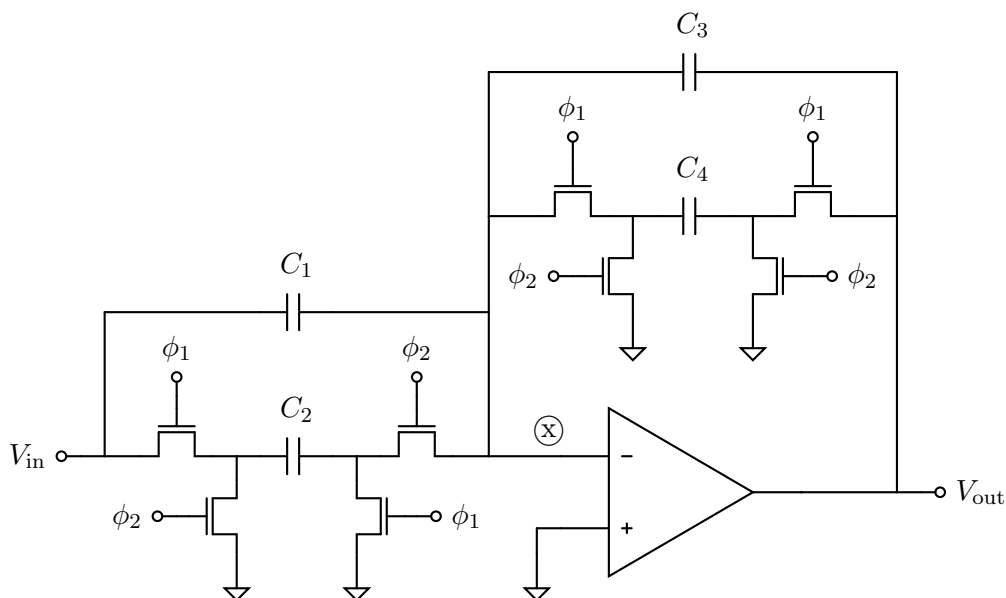


Figure 2: Switched capacitor circuit

All questions in this problem refer to the switched capacitor (SC) circuit in figure 2.

2a Continuous time equivalent 3 %

Draw a continuous time equivalent of this circuit.

2b Frequency response 8 %

Derive an expression for the frequency response given the following transfer function

$$H(z) = \frac{V_{\text{out}}(z)}{V_{\text{in}}(z)} = -\frac{C_1 - (C_1 + C_2)z^{-1}}{(C_4 + C_3) - C_4z^{-1}}$$

(Continued on page 3.)

2c Large time constants 3 %

If large time constants are required for this circuit, is the SC or the continuous time circuit preferable in an integrated circuit application?

2d Precise time constants 3 %

If precisely defined time constants are required for the circuit, is the SC or the continuous time circuit preferable in an integrated circuit application?

2e Poly-poly capacitors 4 %

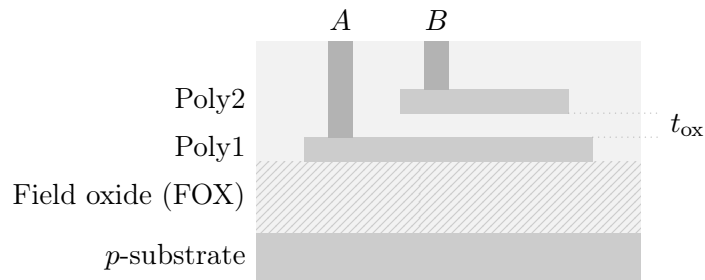


Figure 3: Poly-poly capacitor

The circuit is implemented in an older CMOS process where poly-poly capacitors (see figure 3) are available. Explain why the capacitor is not symmetric with respect to the terminals *A* and *B*. Which terminal would you connect towards node \otimes in the SC circuit?

2f MoM capacitors 4 %

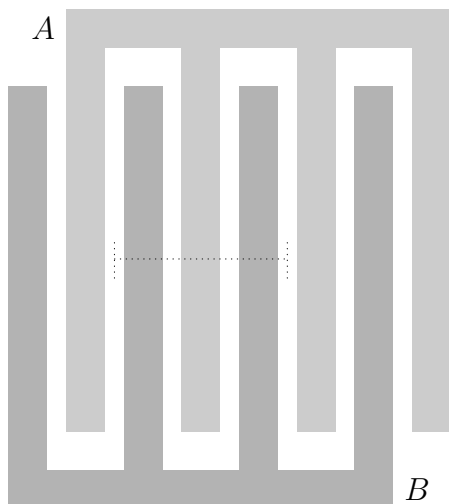


Figure 4: MoM top view

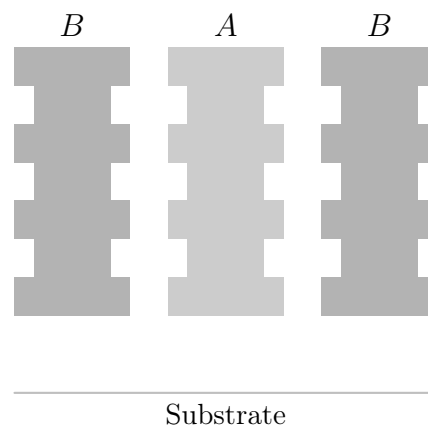


Figure 5: MoM side view

(Continued on page 4.)

If the circuit is implemented in a deep sub-micron (DSM) CMOS process, a metal-oxide-metal (MoM) capacitor (see figure 4 and 5) may be used instead. Explain how you can reduce the parasitic capacitance. What is the trade-off in this case?

Problem 3 Flash ADCs 25 %

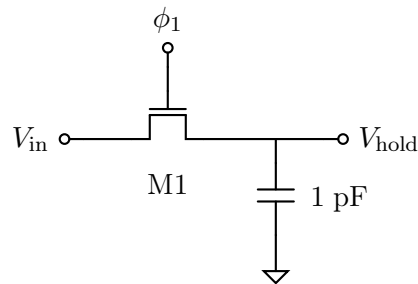


Figure 6: Track and hold (T/H) circuit

3a Track and hold 7 %

The track and hold (T/H) circuit of figure 6 is used as a front end in a flash ADC clocked at 200 MHz with a reference voltage of 1 V. If the settling error can be no larger than 4 mV, what is the highest value the “on” resistance, R_{on} , of M1 can have? (Ignore the body effect.)

3b Sizing 7 %

Assume the circuit is to be implemented in a 0.18 μm process with $\mu_n C_{ox} \approx 328.5 \frac{\mu\text{A}}{\text{V}^2}$ and $V_{TH} = 530 \text{ mV}$. The supply voltage is $V_{dd} = 1.8 \text{ V}$. These are nominal parameters, and you do not have to consider different PVT conditions. How would you choose the size of M1?

3c Resolution 4 %

What is the maximum attainable resolution of the converter if we require the settling error to be less than $\frac{1}{2}$ LSB?

3d Figure of Merit 3 %

If the converter uses 26 mW, what is the figure of merit (FoM)?

3e Time interleaving 4 %

If this converter needs to run at 800 MHz, can time interleaving be used to achieve this?

(Continued on page 5.)

Problem 4 Pipelined ADCs 20 %

4a Offset 7 %

The comparator in the first stage of this converter is implemented in a $0.18\ \mu\text{m}$ process with $t_{\text{ox}} = 4\ \text{nm}$. The input transistors are $W = 12\ \mu\text{m}$ and $L = 0.4\ \mu\text{m}$. What is the standard deviation, σ , of the input referred offset voltage, V_{os} , if the threshold voltage is the most significant source of variability? (Use a reasonable value for A_{VTH} based on the information you have.)

4b Sizing 7 %

The desired resolution of the converter is 8 bit, and the reference voltage is $1.2\ \text{V}$. What is the required size of the input transistors if we only scale the width, and we want the worst case (3σ) V_{os} to be less than $\frac{1}{2}$ LSB?

4c Residue 6 %

Calculate the residue from each stage of a 5 bit pipelined ADC with a reference voltage of $1.2\ \text{V}$ and 1 bit per stage when the input voltage is $340\ \text{mV}$. What is the final digital output? Compare the digital output to the analog input voltage. Is the quantization error less than one LSB?

Problem 5 Current Steering DACs 10 %

5a Switch resistance, R_{on} 4 %

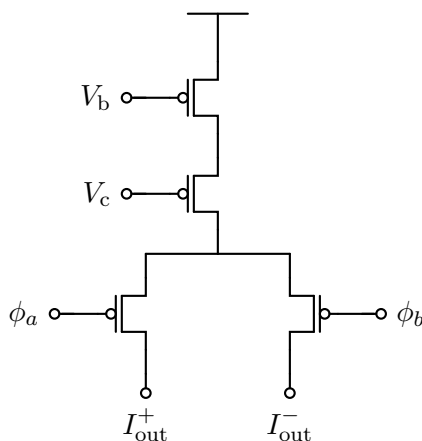


Figure 7: CS DAC unit

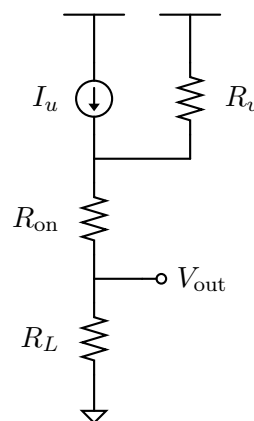


Figure 8: Equivalent circuit

Figure 7 shows one unit of a current steering (CS) DAC, and figure 8 is a simplified model of the same circuit (with an added load resistor). Assume

(Continued on page 6.)

that a high output resistance is required for a given linearity specification. Discuss why or why not the switch resistance, R_{on} , can be used to significantly contribute to the output resistance.

5b CMOS process configurations 6 %

According to [1], present and future CMOS process technology nodes come in different configurations suitable for different applications, such as low power (LP) and high performance (HP). Discuss how choosing a LP or HP process configuration impacts the CS DAC implementation.

References

- [1] L.L. Lewyn, T. Ytterdal, C. Wulff, and K. Martin. Analog Circuit Design in Nanoscale CMOS Technologies. *Proceedings of the IEEE*, 97(10):1687–1714, October 2009.